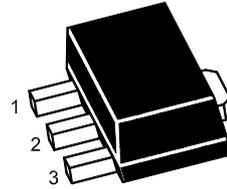


Silicon NPN Epitaxial

Application

- Low frequency power amplifier
- Complementary pair with 2SB1002



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	100	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	1	A
Collector peak current	$i_{C(peak)}^{*1}$	1.5	A
Collector power dissipation	P_C^{*2}	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 ms, Duty cycle ≤ 20%

2. Value on the alumina ceramic board (12.5 x 20 x 0.7 mm)

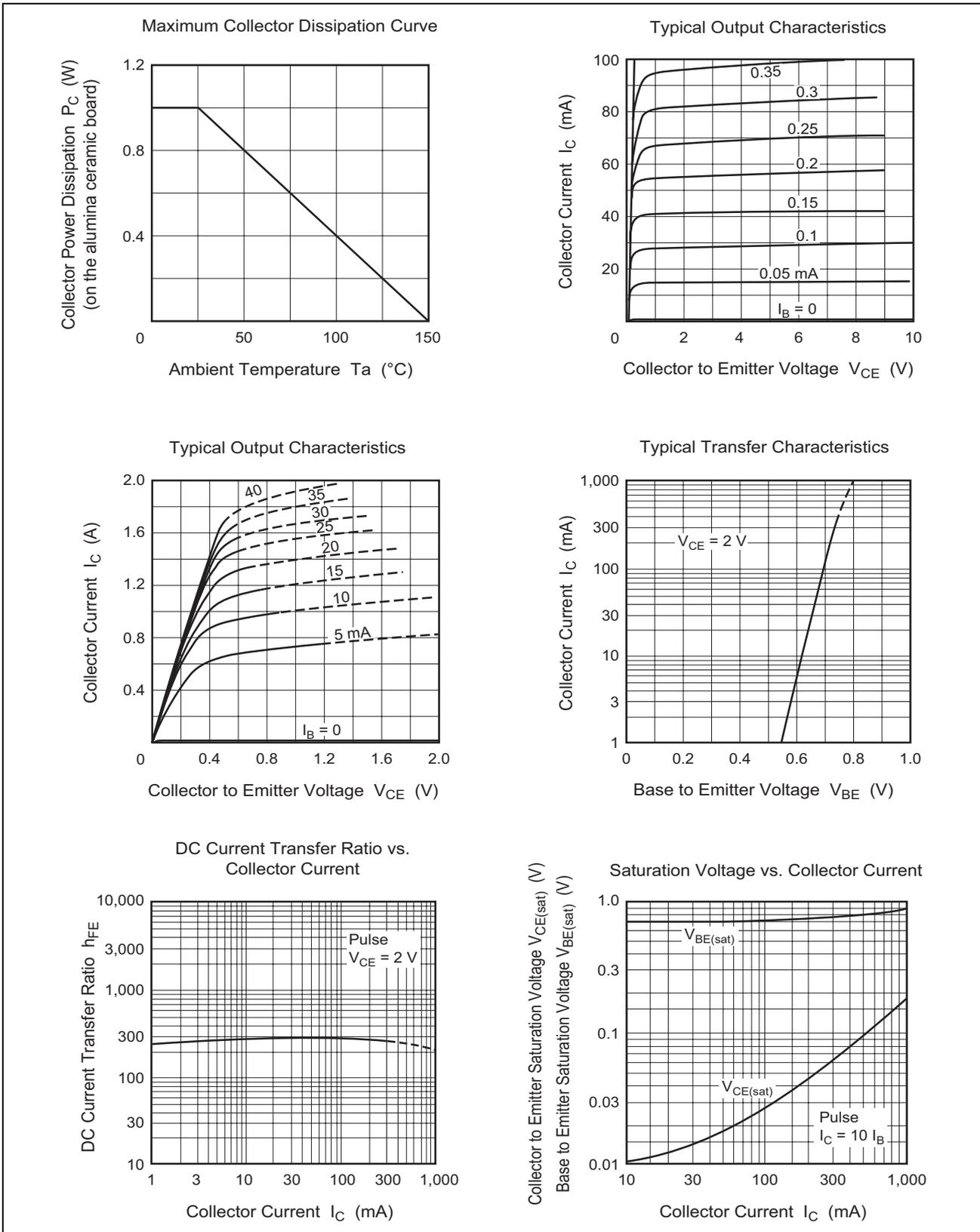
Electrical Characteristics

(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	100	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	—	—	V	$I_C = 1 mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.1	μA	$V_{CB} = 80 V, I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.1	μA	$V_{EB} = 4 V, I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	160	—	500		$V_{CE} = 2 V, I_C = 0.1 A$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C = 1 A, I_B = 0.1 A, \text{Pulse}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.2	V	$I_C = 1 A, I_B = 0.1 A, \text{Pulse}$
Gain bandwidth product	f_T	—	100	—	MHz	$V_{CE} = 2 V, I_C = 10 mA, \text{Pulse}$
Collector output capacitance	C_{ob}	—	20	—	pF	$V_{CB} = 10 V, I_E = 0, f = 1 MHz$

Note: 1. The 2SD1368 is grouped by h_{FE} as follows.

Mark	CB	CC
h_{FE}	160 to 320	250 to 500

2SD1368
Main Characteristics


2SD1368

